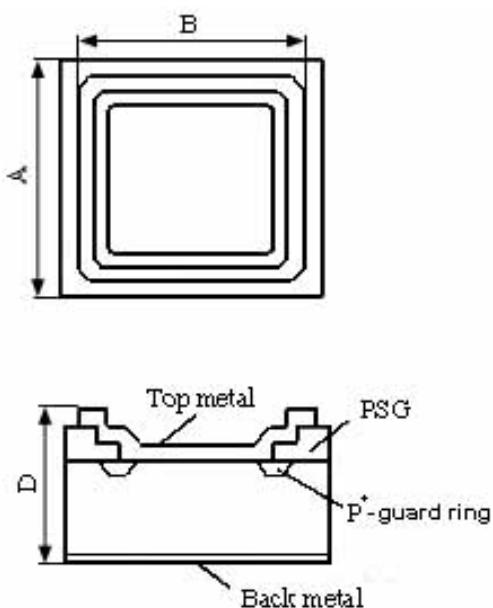


# SCHOTTKY DIODES **KD 291S6.**



Rev.2. July. 2010

<b>VSP-MIKRON</b>	<b>4A/200V. Die Size-65mil.</b>			
<b>Electrical Characteristics</b>	<b>Symbol</b>	<b>Unit</b>	<b>Spec. limit</b>	<b>Die Sort</b>
Breakdown Voltage @ $I_R=10mA$	$V_{BR}$	V	200	210
Average Rectified Forward Current	$I_{F(AV)}$	A	4,0	-
DC Forward Voltage @ 25°C, $I_F=4,0A$	$V_F$	V	0,86	0,84
Maximum Reverse Current @ 25°C, $V_R=200V$ 125°C, $V_R=200V$	$I_R$	mA	0,005 5,0	0,003 4,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	110	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., $T_J<175^\circ C$ .	$I_{RRM}$	A	2,0	
Reverse Recovery Time, $I_F=1A, V_R=30V, dI_F/dt=100A/uS$ .	$t_{rr}$	nS	35	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	$V_{ESD}$	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	$T_J$	°C	175	



<b>DIM</b>	<b>ITEM</b>	<b>µm</b>
$A_x$ $A_y$	Wafer Form Die Size	1650 1650
$B_x$ $B_y$	Top Metal Size	1510 1510
D	Thickness	300max.
Scribe line Width		80

*Top metal:* a) **Al-Ni-Ag** – for Soldering;  
b) **Al** – for Wire Bonding.

*Backside metal:* **Ti-Ni-Ag.**